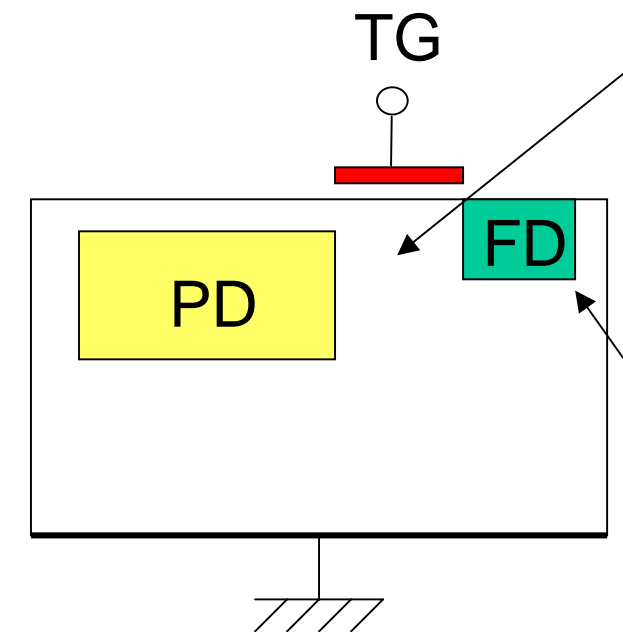


Device Simulation with Electromagnetic Field Propagation Models for High-Speed Image Sensors and FDA Noise Analysis

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Why electromagnetic field propagation should be considered?



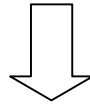
CMOS Image Sensor

(1) Field propagation delay cannot be ignored in ultra-high speed image sensors

(2) FDA noise is induced by multi-reflected electric field wave packet

Are Maxwell's equations correct?

Charge conservation & principle of superposition



Carrier generation-recombination is forbidden

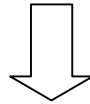
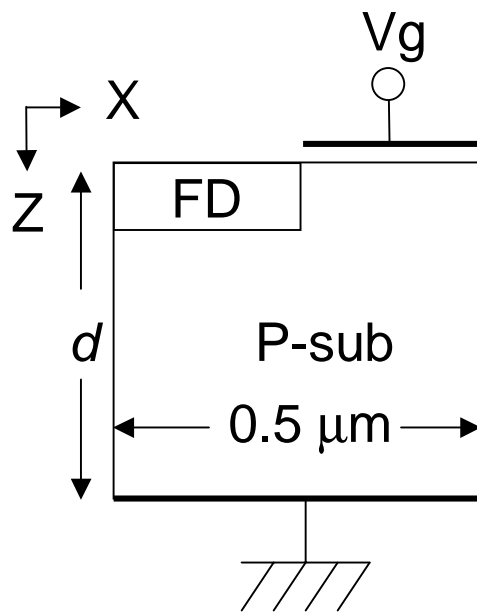


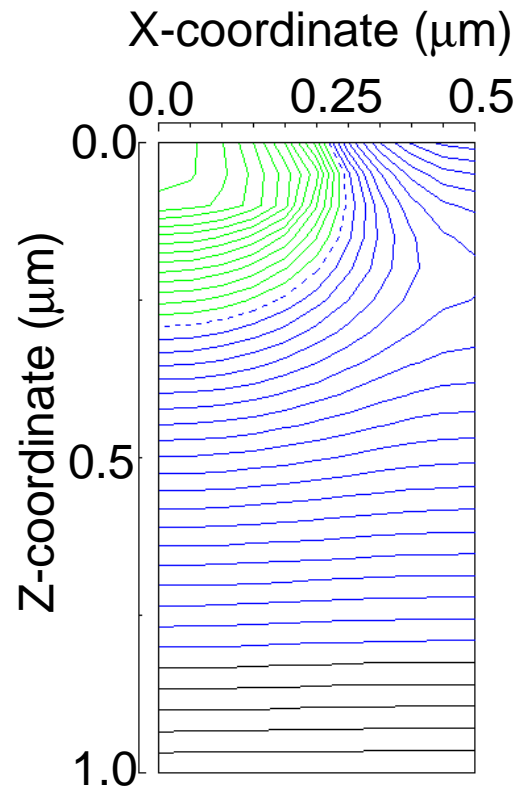
Image sensors cannot work

Maxwell	Scalar field	QED equivalent
$\left. \begin{aligned} \mathbf{J} &= \nabla \times \mathbf{H} - \epsilon \frac{\partial \mathbf{E}}{\partial t} \\ \rho &= \epsilon \nabla \cdot \mathbf{E} \end{aligned} \right\}$	$\gamma \equiv \nabla \cdot \mathbf{A} + \frac{1}{c^2} \frac{\partial \psi}{\partial t}$	$\left\{ \begin{aligned} \mathbf{J} &= \nabla \times \mathbf{H} - \epsilon \frac{\partial \mathbf{E}}{\partial t} - \frac{1}{\mu} \nabla \gamma \\ \rho &= \epsilon \nabla \cdot \mathbf{E} + \epsilon \frac{\partial \gamma}{\partial t} \end{aligned} \right.$
\Downarrow $GR = \nabla \cdot \mathbf{J} + \frac{\partial \rho}{\partial t} = 0$	\Rightarrow	\Downarrow $GR = \nabla \cdot \mathbf{J} + \frac{\partial \rho}{\partial t} = -\frac{1}{\mu} \square \gamma$

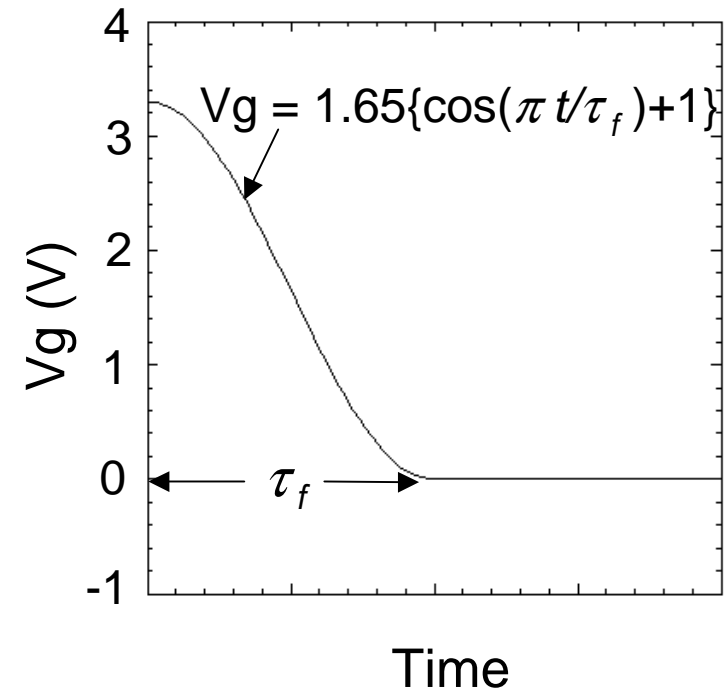
FDA Noise Analysis



Structure



Potential
($d = 1 \mu\text{m}$)



V_g dependence on time

FDA noise dependence on substrate thickness

(Wave packet length : $\lambda_p \equiv \tau_f c / n_{\text{si}}$)

